Author's Accepted Manuscript

Nanostructured SiC prepared by ultra low temperature densification using amorphous/nano-crystalline bimodal Si-Al-C powder

Bola Yoon, Sea-Hoon Lee, Lin Zhao, Heesoo Lee



 PII:
 S0272-8842(18)31301-4

 DOI:
 https://doi.org/10.1016/j.ceramint.2018.05.157

 Reference:
 CERI18332

To appear in: Ceramics International

Received date: 10 April 2018 Revised date: 8 May 2018 Accepted date: 17 May 2018

Cite this article as: Bola Yoon, Sea-Hoon Lee, Lin Zhao and Heesoo Lee, Nanostructured SiC prepared by ultra low temperature densification using amorphous/nano-crystalline bimodal Si-Al-C powder, *Ceramics International*, https://doi.org/10.1016/j.ceramint.2018.05.157

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting galley proof before it is published in its final citable form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.

ACCEPTED MANUSCRIPT

Nanostructured SiC prepared by ultra low temperature densification using amorphous/nano-crystalline bimodal Si-Al-C powder

Bola Yoon^{1,2}, Sea-Hoon Lee^{1*} Lin Zhao¹, Heesoo Lee³

¹Division of Powder and Ceramics Research, Korea Institute of Materials Science, Changwon 51508, Republic of Korea

²Materials Science and Engineering Program, Department of Mechanical Engineering, University of Colorado Boulder, Boulder, CO 80309, United States

³Department of Materials Science and Engineering, Pusan National University, Busan 609-735, Republic of Korea

*Corresponding author. seahoon1@kims.re.kr

Abstract

Mechanical alloying and spark plasma sintering were used to fabricate dense and nanostructured SiC at 1525°C under 40 MPa pressure. Round-shaped nanopowder (d_{50} : 108 nm) consisting of amorphous Si-Al-C and β -SiC crystallites was prepared using high-energy ball-milling. Aluminum was homogeneously distributed in the Si-Al-C powder. The addition of Al during the milling process caused the decrement in the 3C-SiC crystallinity and promoted the generation of stacking faults in 3C-SiC. Dense SiC with the grain size of 132 nm was fabricated after a two-step sintering at 1600-1550°C. The Al content in the sintered SiC grain was more than 3 times higher than the reported values. Grain boundary diffusion and lattice diffusion were activated due to the high concentration of Al in the powder.

Keywords: Stacking faults, Mechanical alloying, Raman spectroscopy, Spark plasma sintering, Carbides

Download English Version:

https://daneshyari.com/en/article/7886109

Download Persian Version:

https://daneshyari.com/article/7886109

Daneshyari.com